

Amendments to the Specification:

Please replace the abstract at page 11 with the following amended abstract:

~~--Radiation emitting semiconductor component~~

In a radiation-emitting semiconductor component with a layer structure comprising an n-doped confinement layer [(14)], a p-doped confinement layer [(22)], and an active, photon-emitting layer [(18)] disposed between the n-doped confinement layer [(14)] and the p-doped confinement layer [(22)], it is provided according to the invention that the n-doped confinement layer [(14)] is doped with a first n-dopant (or two mutually different n-dopants) for producing high active doping and a sharp doping profile, and the active layer [(18)] is doped with only one second n-dopant, different from the first dopant, for improving the layer quality of the active layer [(18)].

~~Figure 1--~~